

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device may include a first internal circuit operating at a first voltage higher than a power supply voltage of the device, and a second internal circuit operating at a second voltage lower than the first voltage. An interface circuit may be provided to restrict a voltage transferred from the first internal circuit to the second internal circuit. The first internal circuit may include a metal oxide semiconductor (MOS) transistor having a relatively thick gate insulation layer, and the second internal circuit may have a MOS transistor having a relatively thin gate insulation layer. The interface circuit, by restricting voltage, may reduce an electric field applied to the gate insulation layer of the second MOS transistor in an effort to prevent a reduction in turn-on speed of the second MOS transistor.